

SUBSTITUTE FORM PTO-1449 (MODIFIED)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. BEET/09	SERIAL NO. 10/524,525
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary) (37 CFR 1.98(b))				APPLICANT Martin Hausner	
				FILING DATE February 11, 2005	CONFIRMATION NO. 1134

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A.A						
	A.B						
	A.C						
	A.D						
	A.E			APR 19 2005			
	A.F						
	A.G						
	A.H						
	A.I						
	A.J						
	A.K						

FOREIGN PATENTS OR PUBLISHED FOREIGN PATENT APPLICATIONS

		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION (YES/NO)
/SA/	A.L	KR 2002041363A	06/2002	Republic of Korea	H01L	21/3065	No
	A.M						
	A.N						
	A.O						
	A.P						
	A.Q						

OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication)

/SA/	A.R	Ayon et al., <u>Characterization of a Time Multiplexed Inductively Coupled Plasma Etcher</u> , Journal of the Electrochemical Society, January 1999, Vol. 146, Issue 1, pp. 339-349
/SA/	A.S	The International Bureau of WIPO, <u>English Translation of the International Preliminary Examination Report</u> , November 17, 2004 (12 pages)
	A.T	

EXAMINER /Shamim Ahmed/ (04/11/2007)	DATE CONSIDERED 04/11/2007
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EXAMINER: Initial if citation considered, whether or not in conformance. Draw line through citation only if not in conformance and not considered. Include a copy of this form with next communication to applicant.

BT01 Rec'd PCT/PTC 11 FEB 2005

Sheet 1 (A) of 5

SUBSTITUTE FORM PTO-1449 (MODIFIED)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE						ATTY/AGEN	RECEIPT NO. BEET/09	EXPRESS MAIL NO. EV/P561458504
		INFORMATION DISCLOSURE STATEMENT BY APPLICANT						APPLICANT Martin Hausner		
		(Use several sheets if necessary) (37 CFR 1.98(b))						FILING DATE February 11, 2005		GROUP Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER						ISSUE DATE	PATENTEE		CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
/SA/	A.A	6	0	7	4	9	4	6	06/2000	Ouellet et al.	438	689	02/1997
/SA/	A.B	6	4	5	8	6	1	5	10/2002	Fedder et al.	438	50	09/1999
	A.C												
	A.D												
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	A.F												
	A.G												
	A.H												
	A.I												
	A.J												
	A.K												

FOREIGN PATENTS OR PUBLISHED FOREIGN PATENT APPLICATIONS.

		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION (YES/NO)
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	A.M	DE 197 36 370 C2	12/2001	Germany	H01L	21/3065	No
	A.N	DE 199 00 179 C1	02/2000	Germany	C23F	4/00	No
	A.O	DE 199 27 806 A1	01/2001	Germany	H01L	21/3065	No
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/SA/	A.R	Ayon et al., Anisotropic silicon trenches 300-500 um deep employing time multiplexed deep etching (TMDE). Sensors and Actuators A, Vol. 91, 2001, pp. 381-385
/SA/	A.S	Database WPI, A method of through-etching substrate is provided to efficiently perform a cooling processing of a substrate and to improve a profile around a penetrated hole by using a metal material, Section Ch, Week 200278, Derwent Publications Ltd., London, GB, Class L03, AN 2002-720751 (1 page)
/SA/	A.T	Dijkstra et al., Can SEA (Semiconductor Equipment Assessment) also deliver for MEMS?, Horological Journal, Ashford, GB, Vol. 556, No. 302, 2001, pp. 684-690

EXAMINER		DATE CONSIDERED
	/Shamim Ahmed/ (04/11/2007)	04/11/2007

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